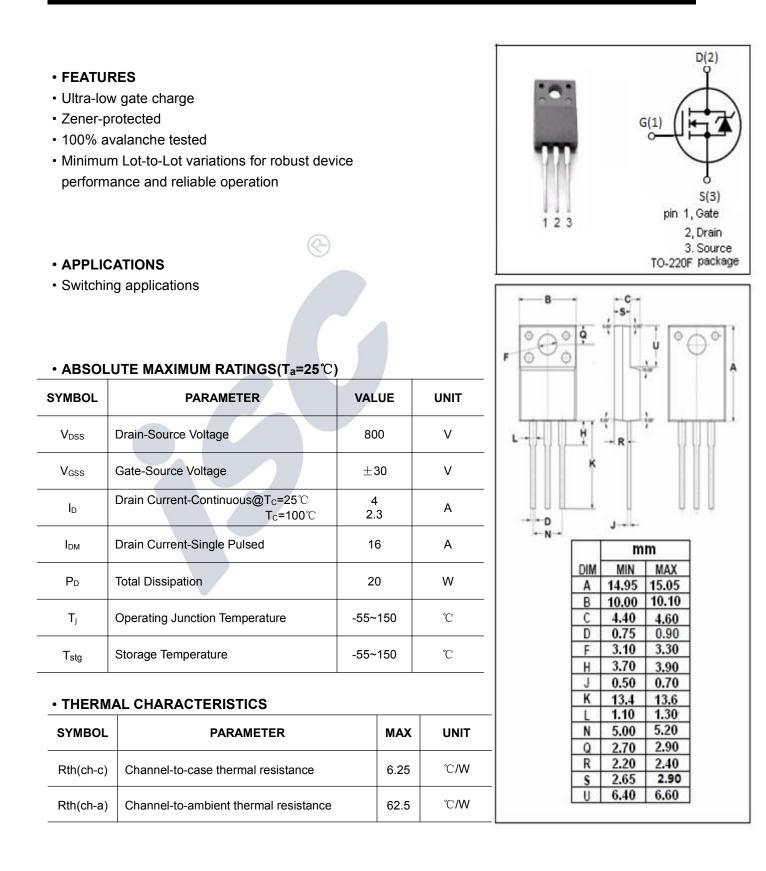


INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

STF5N80K5



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STF5N80K5

ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	800			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.1mA	3		5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2A		1.50	1.75	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±10	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V; T _J =25℃ T _J =125℃			1 50	μ Α
V _{SDF}	Diode forward voltage	I _{SD} =4A, V _{GS} = 0 V			1.6	v



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